

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	12090	(polySi or polysilicon or ((poly or polycrystalline) adj (Si or silicon))) same (trench or groove or recess\$6 or interconnect\$6) same source	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/06 12:08
L2	12001	1 and (memory or semiconductor or transistor or MOSFET or FET or NMOS or PMOS or CMOS)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/06 11:29
L3	11185	2 and (@ad<="20031117" or @rlad<="20031117")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/06 11:30
L4	3272	3 and ((polySi or polysilicon or ((poly or polycrystalline) adj (Si or silicon))) with (trench or groove or recess\$6 or interconnect\$6) with source)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/06 12:06
L5	1089	4 and ((polySi or polysilicon or ((poly or polycrystalline) adj (Si or silicon))) same (trench or groove or recess\$6 or interconnect\$6) same source same (mask\$6 or resist or photoresist))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/06 12:08
L6	992	5 and ((polySi or polysilicon or ((poly or polycrystalline) adj (Si or silicon))) with (pattern\$6 or etch\$6 or remov\$6))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/04/06 12:09